

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	31906	("sulfuric acid" and "hydrogen peroxide" "di water")	US-PGPUB; USPAT	OR	OFF	2005/06/06 15:06
L2	30	("sulfuric acid" with "hydrogen peroxide" with "di water")	US-PGPUB; USPAT	OR	OFF	2005/06/06 15:29
L3	3114	((dip\$4 vertical\$2 (up and down)) with (bath etch tank)) with (wafer substrate semiconductor)	USPAT	OR	OFF	2005/06/06 15:29
L4	1254	L3 and ("134"/\$ 156/345.\$ "216"/\$ "438"/\$)	USPAT	OR	OFF	2005/06/06 15:29
L5	78	L4 and rpm	US-PGPUB; USPAT	OR	OFF	2005/06/06 15:29
S1	10733	134/113 156/345 156/345.\$ 156/8 216/88 216/89 216/90 216/83	USPAT	OR	OFF	2005/06/06 13:19
S2	767	216/100 216/95 216/91	USPAT	OR	OFF	2005/05/17 13:20
S3	11147	S1 S2	USPAT	OR	OFF	2005/05/17 13:20
S4	2031	S3 and (semiconductor wafer substrate) with (vertical\$2 nonhorizontal)	USPAT	OR	OFF	2005/05/17 13:22
S5	1648	S4 and (etch\$3 dip\$4 bath container)	USPAT	OR	OFF	2005/05/17 13:22
S6	1061	S5 and (metal copper)	USPAT	OR	OFF	2005/05/17 13:23
S7	198	S5 and (metal copper) same (edge peripher\$4)	USPAT	OR	OFF	2005/05/17 14:18
S8	29674	wet with etch\$3	USPAT	OR	OFF	2005/05/17 14:18
S9	574	S8 with vertical\$2	USPAT	OR	OFF	2005/05/17 14:19
S10	45100	(dip\$4 wet immers\$4) with (wafer substrate semiconductor)	USPAT	OR	OFF	2005/05/17 14:20
S11	668	S10 with vertical\$2	USPAT	OR	OFF	2005/06/03 15:10
S12	1107	S9 S11	USPAT	OR	OFF	2005/05/17 14:20
S13	43712	chuck sme bath same (semiconductor wafer)	USPAT	OR	OFF	2005/05/31 14:03
S14	97	chuck same bath same (semiconductor wafer)	USPAT	OR	OFF	2005/05/31 14:16
S15	3	("6625835" "20030209255" "20020040888" "6290865" "3898095").pn.	USPAT	OR	OFF	2005/05/31 14:17
S16	5	("6625835" "20030209255" "20020040888" "6290865" "3898095").pn.	US-PGPUB; USPAT	OR	OFF	2005/05/31 14:17
S17	3195	"taiwan semiconductor manufacturing"	USPAT	OR	OFF	2005/05/31 14:45
S18	4	S17 and (chuck same bath)	USPAT	OR	OFF	2005/05/31 14:44
S19	2499	S17 and (bath tank dip\$4 etch\$3)	USPAT	OR	OFF	2005/05/31 14:45

S20	544	S19 and (chuck holder table)	USPAT	OR	OFF	2005/05/31 14:45
S21	179	"taiwan semiconductor manufacturing" and (bath tank dip\$4 etch\$3) same (chuck holder table)	USPAT	OR	OFF	2005/05/31 15:37
S22	728	134/113	USPAT	OR	OFF	2005/05/31 14:56
S23	172	S22 and (semiconductor wafer)	USPAT	OR	OFF	2005/05/31 15:20
S24	1716	(sccm "ml/min") same etch\$3 same (wafer semiconductor)	USPAT	OR	OFF	2005/05/31 15:37
S25	977	(sccm "ml/min") with etch\$3 same (wafer semiconductor)	USPAT	OR	OFF	2005/05/31 15:23
S26	5	S25 same (bath tank)	USPAT	OR	OFF	2005/05/31 15:26
S27	71	S17 and S25	USPAT	OR	OFF	2005/05/31 15:27
S28	3	S27 not plasma	USPAT	OR	OFF	2005/05/31 15:28
S29	97	S25 not (plasma)	USPAT	OR	OFF	2005/05/31 15:28
S30	94	S29 not S28	USPAT	OR	OFF	2005/05/31 15:28
S31	78	(sccm "ml/min") and S21	USPAT	OR	OFF	2005/05/31 15:42
S32	41148	"ml/min"	USPAT	OR	OFF	2005/05/31 15:50
S33	1908	S32 and etch\$3	USPAT	OR	OFF	2005/05/31 15:42
S34	384	S33 and (fluid not plasma)	USPAT	OR	OFF	2005/05/31 15:43
S35	3539	"ml/min" with (fluid liquid)	USPAT	OR	OFF	2005/05/31 15:50
S36	9	S35 same etch\$3	USPAT	OR	OFF	2005/05/31 15:52
S37	1	"6051505".pn	USPAT	OR	OFF	2005/05/31 15:54
S38	1	S37 and sccm	USPAT	OR	OFF	2005/05/31 15:52
S39	45275	(dip\$4 wet immers\$4) with (wafer substrate semiconductor)	USPAT	OR	OFF	2005/06/03 15:10
S40	673	S39 with vertical\$2	USPAT	OR	OFF	2005/06/03 15:11
S41	82463	((dip\$4 vertical\$2 (up and down)) and (bath etch tank)) and (wafer substrate semiconductor)	USPAT	OR	OFF	2005/06/06 10:02
S42	9613	((dip\$4 vertical\$2 (up and down)) same (bath etch tank)) same (wafer substrate semiconductor)	USPAT	OR	OFF	2005/06/06 10:03
S43	3114	((dip\$4 vertical\$2 (up and down)) with (bath etch tank)) with (wafer substrate semiconductor)	USPAT	OR	OFF	2005/06/06 10:04
S44	1254	S43 and ("134"/\$ 156/345.\$ "216"/\$ "438"/\$)	USPAT	OR	OFF	2005/06/06 10:06
S45	14	"20020040888" "3898095"	USPAT	OR	OFF	2005/06/06 13:20
S46	1	"20020040888"	US-PGPUB; USPAT	OR	OFF	2005/06/06 15:05